

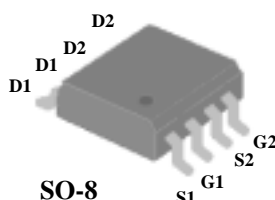


N AND P-CHANNEL ENHANCEMENT  
MODE POWER MOSFET

▼ Simple Drive Requirement

▼ Low On-resistance

▼ Fast Switching

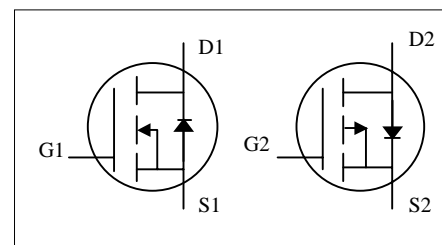


N-CH	$BV_{DSS}$	30V
	$R_{DS(ON)}$	28m $\Omega$
	$I_D$	7A
P-CH	$BV_{DSS}$	-30V
	$R_{DS(ON)}$	50m $\Omega$
	$I_D$	-5.3A

## Description

The Advanced Power MOSFETs from APEC provide the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost-effectiveness.

The SO-8 package is universally preferred for all commercial-industrial surface mount applications and suited for low voltage applications such as DC/DC converters.



## Absolute Maximum Ratings

Symbol	Parameter	Rating		Units
		N-channel	P-channel	
$V_{DS}$	Drain-Source Voltage	30	-30	V
$V_{GS}$	Gate-Source Voltage	$\pm 20$	$\pm 20$	V
$I_D @ T_A = 25^\circ\text{C}$	Continuous Drain Current <sup>3</sup>	7	-5.3	A
$I_D @ T_A = 70^\circ\text{C}$	Continuous Drain Current <sup>3</sup>	5.8	-4.7	A
$I_{DM}$	Pulsed Drain Current <sup>1</sup>	20	-20	A
$P_D @ T_A = 25^\circ\text{C}$	Total Power Dissipation	2		W
	Linear Derating Factor	0.016		W/ $^\circ\text{C}$
$T_{STG}$	Storage Temperature Range	-55 to 150		$^\circ\text{C}$
$T_J$	Operating Junction Temperature Range	-55 to 150		$^\circ\text{C}$

## Thermal Data

Symbol	Parameter	Value	Unit
Rthj-amb	Thermal Resistance Junction-ambient <sup>3</sup>	Max.	62.5 $^\circ\text{C}/\text{W}$



## AP4501M

### N-CH Electrical Characteristics @ $T_j=25^\circ\text{C}$ (unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
$BV_{DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	30	-	-	V
$\Delta BV_{DSS}/\Delta T_j$	Breakdown Voltage Temperature Coefficient	Reference to $25^\circ\text{C}$ , $I_D=1\text{mA}$	-	0.02	-	$V/^\circ\text{C}$
$R_{DS(ON)}$	Static Drain-Source On-Resistance <sup>2</sup>	$V_{GS}=10V, I_D=7A$	-	-	28	$\text{m}\Omega$
		$V_{GS}=4.5V, I_D=5A$	-	-	42	$\text{m}\Omega$
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu A$	1	-	3	V
$g_{fs}$	Forward Transconductance	$V_{DS}=10V, I_D=7A$	-	13	-	S
$I_{DSS}$	Drain-Source Leakage Current ( $T_j=25^\circ\text{C}$ )	$V_{DS}=30V, V_{GS}=0V$	-	-	1	$\mu A$
	Drain-Source Leakage Current ( $T_j=70^\circ\text{C}$ )	$V_{DS}=24V, V_{GS}=0V$	-	-	25	$\mu A$
$I_{GSS}$	Gate-Source Leakage	$V_{GS}=\pm 20V$	-	-	$\pm 100$	nA
$Q_g$	Total Gate Charge <sup>2</sup>	$I_D=7A$	-	8.4	-	nC
$Q_{gs}$	Gate-Source Charge	$V_{DS}=24V$	-	2.1	-	nC
$Q_{gd}$	Gate-Drain ("Miller") Charge	$V_{GS}=4.5V$	-	4.7	-	nC
$t_{d(on)}$	Turn-on Delay Time <sup>2</sup>	$V_{DS}=15V$	-	6	-	ns
$t_r$	Rise Time	$I_D=1A$	-	5.2	-	ns
$t_{d(off)}$	Turn-off Delay Time	$R_G=3.3\Omega, V_{GS}=10V$	-	18.8	-	ns
$t_f$	Fall Time	$R_D=15\Omega$	-	4.4	-	ns
$C_{iss}$	Input Capacitance	$V_{GS}=0V$	-	645	-	pF
$C_{oss}$	Output Capacitance	$V_{DS}=25V$	-	150	-	pF
$C_{rss}$	Reverse Transfer Capacitance	$f=1.0\text{MHz}$	-	95	-	pF

### Source-Drain Diode

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
$I_S$	Continuous Source Current ( Body Diode )	$V_D=V_G=0V, V_S=1.2V$	-	-	1.67	A
$V_{SD}$	Forward On Voltage <sup>2</sup>	$T_j=25^\circ\text{C}, I_S=7A, V_{GS}=0V$	-	-	1.2	V



### P-CH Electrical Characteristics @T<sub>j</sub>=25°C (unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>D</sub> =-250uA	-30	-	-	V
ΔBV <sub>DSS</sub> /ΔT <sub>j</sub>	Breakdown Voltage Temperature Coefficient	Reference to 25°C, I <sub>D</sub> =-1mA	-	-0.028	-	V/°C
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance <sup>2</sup>	V <sub>GS</sub> =-10V, I <sub>D</sub> =-5.3A	-	-	50	mΩ
		V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-4.2A	-	-	90	mΩ
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =-250uA	-1	-	-3	V
g <sub>fs</sub>	Forward Transconductance	V <sub>DS</sub> =-10V, I <sub>D</sub> =-5.3A	-	8.5	-	S
I <sub>DSS</sub>	Drain-Source Leakage Current (T <sub>j</sub> =25°C)	V <sub>DS</sub> =-30V, V <sub>GS</sub> =0V	-	-	-1	uA
	Drain-Source Leakage Current (T <sub>j</sub> =70°C)	V <sub>DS</sub> =-24V, V <sub>GS</sub> =0V	-	-	-25	uA
I <sub>GSS</sub>	Gate-Source Leakage	V <sub>GS</sub> =±20V	-	-	±100	nA
Q <sub>g</sub>	Total Gate Charge <sup>2</sup>	I <sub>D</sub> =-5.3A	-	20	-	nC
Q <sub>gs</sub>	Gate-Source Charge	V <sub>DS</sub> =-15V	-	3.5	-	nC
Q <sub>gd</sub>	Gate-Drain ("Miller") Charge	V <sub>GS</sub> =-10V	-	2	-	nC
t <sub>d(on)</sub>	Turn-on Delay Time <sup>2</sup>	V <sub>DS</sub> =-15V	-	12	-	ns
t <sub>r</sub>	Rise Time	I <sub>D</sub> =-1A	-	20	-	ns
t <sub>d(off)</sub>	Turn-off Delay Time	R <sub>G</sub> =6Ω, V <sub>GS</sub> =-10V	-	45	-	ns
t <sub>f</sub>	Fall Time	R <sub>D</sub> =15Ω	-	27	-	ns
C <sub>iss</sub>	Input Capacitance	V <sub>GS</sub> =0V	-	790	-	pF
C <sub>oss</sub>	Output Capacitance	V <sub>DS</sub> =-15V	-	440	-	pF
C <sub>rss</sub>	Reverse Transfer Capacitance	f=1.0MHz	-	120	-	pF

### Source-Drain Diode

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
I <sub>S</sub>	Continuous Source Current ( Body Diode )	V <sub>D</sub> =V <sub>G</sub> =0V, V <sub>S</sub> =-1.2V	-	-	-1.67	A
V <sub>SD</sub>	Forward On Voltage <sup>2</sup>	T <sub>j</sub> =25°C, I <sub>S</sub> =-2.6A, V <sub>GS</sub> =0V	-	-	-1.2	V

#### Notes:

1. Pulse width limited by Max. junction temperature.
2. Pulse width ≤300us, duty cycle ≤2%.
3. Surface mounted on 1 in<sup>2</sup> copper pad of FR4 board; 135°C/W when mounted on Min. copper pad.



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## N-Channel

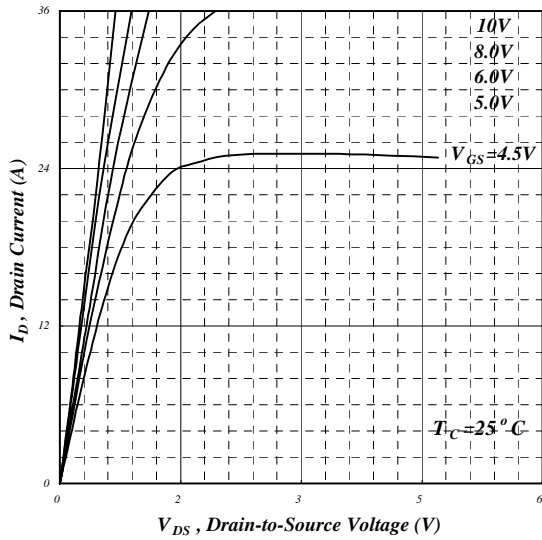


Fig 1. Typical Output Characteristics

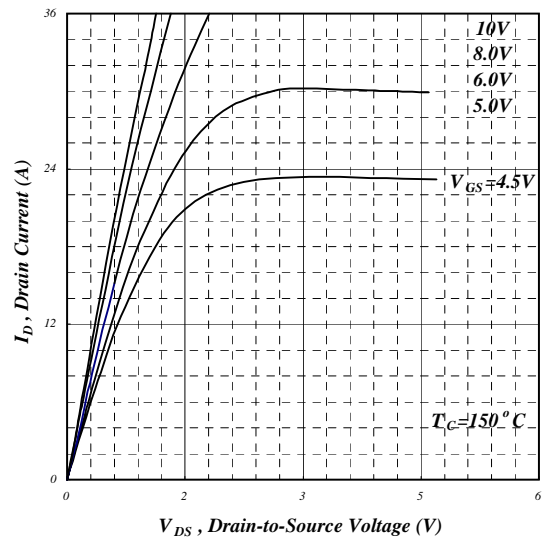


Fig 2. Typical Output Characteristics

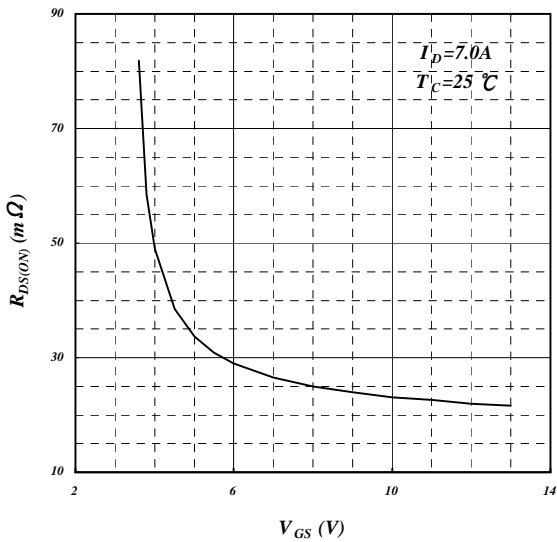


Fig 3. On-Resistance v.s. Gate Voltage

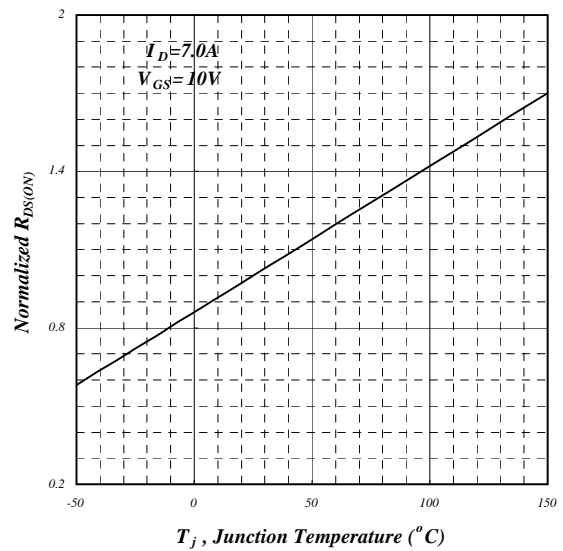


Fig 4. Normalized On-Resistance v.s. Junction Temperature



N-Channel

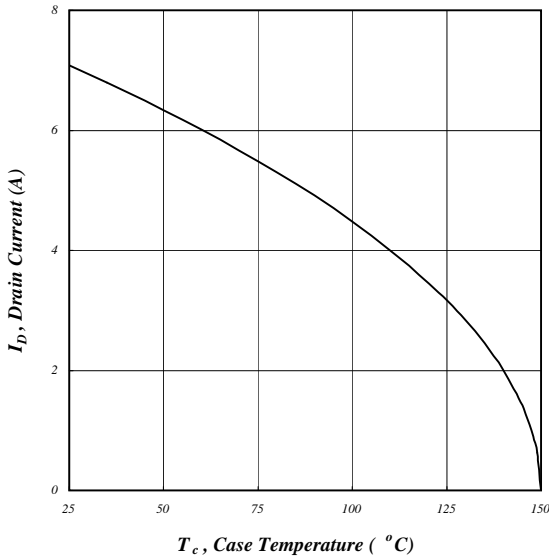


Fig 5. Maximum Drain Current v.s. Case Temperature

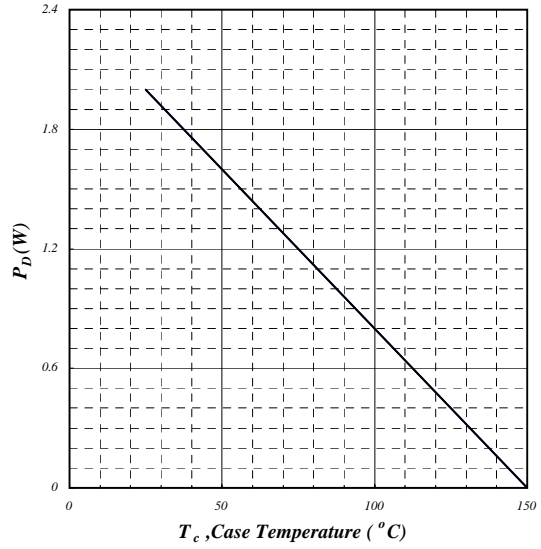


Fig 6. Typical Power Dissipation

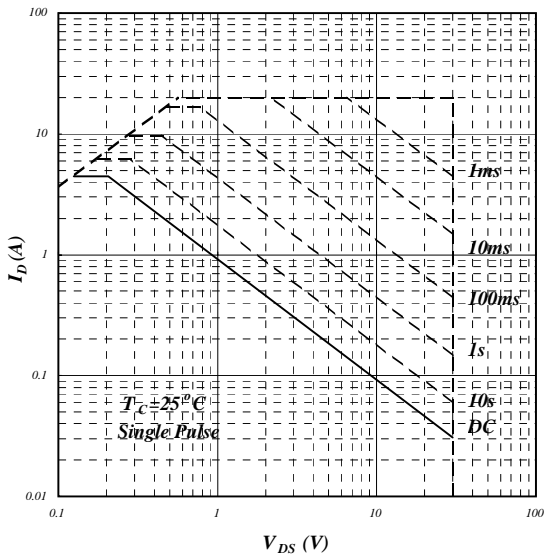


Fig 7. Maximum Safe Operating Area

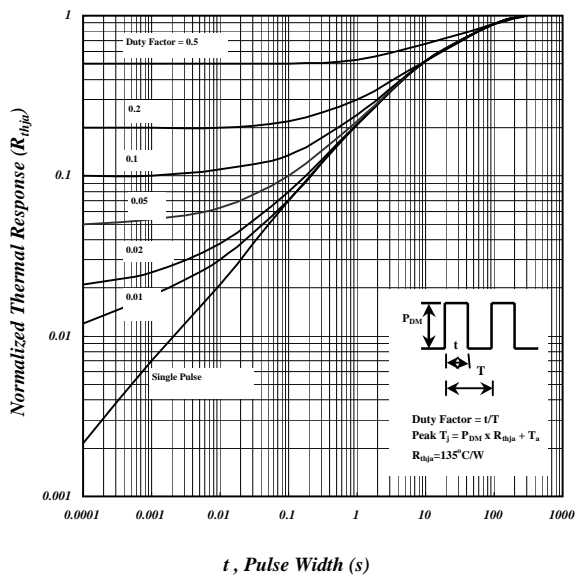


Fig 8. Effective Transient Thermal Impedance



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## N-Channel

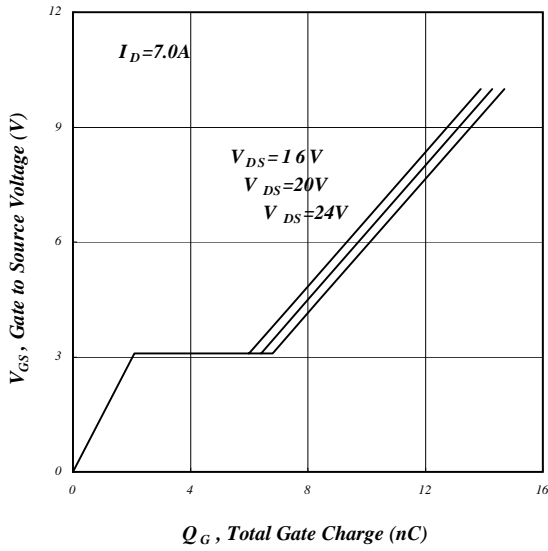


Fig 9. Gate Charge Characteristics

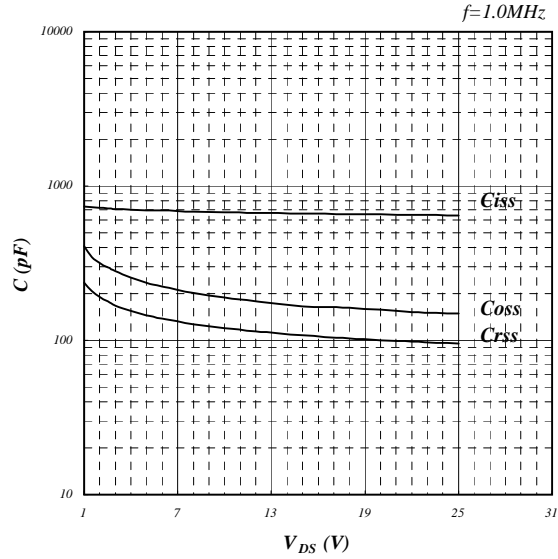


Fig 10. Typical Capacitance Characteristics

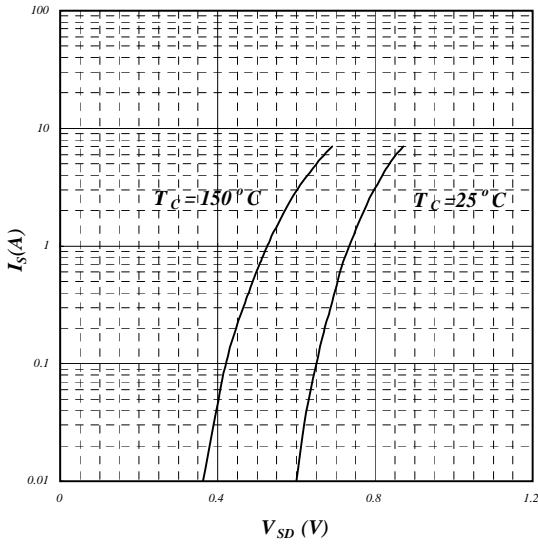


Fig 11. Forward Characteristic of Reverse Diode

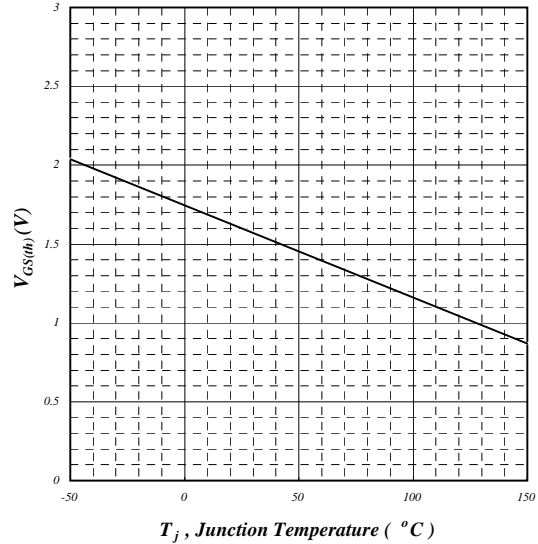


Fig 12. Gate Threshold Voltage v.s. Junction Temperature



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## N-Channel

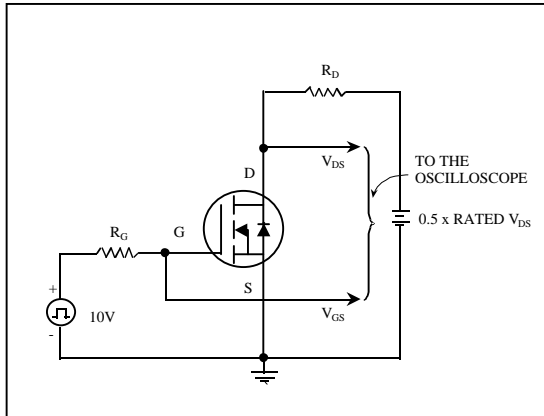


Fig 13. Switching Time Circuit

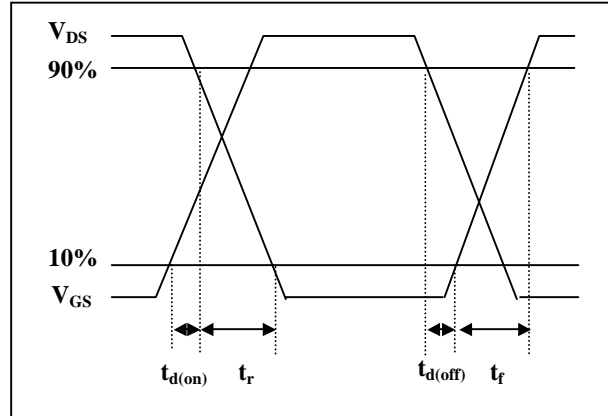


Fig 14. Switching Time Waveform

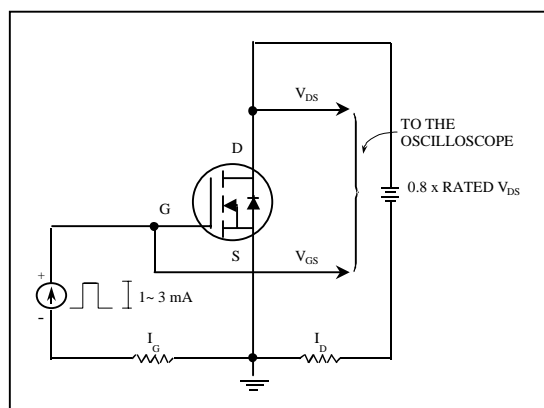


Fig 15. Gate Charge Circuit

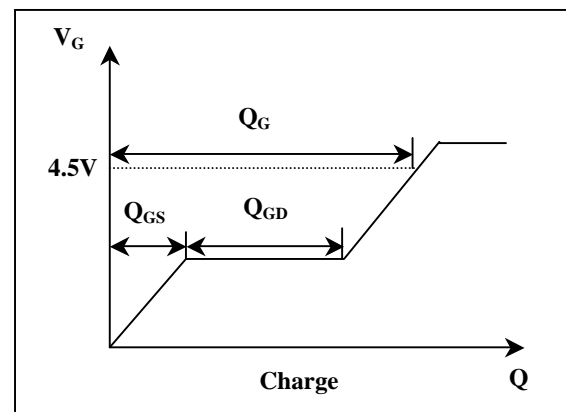


Fig 16. Gate Charge Waveform



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## P-Channel

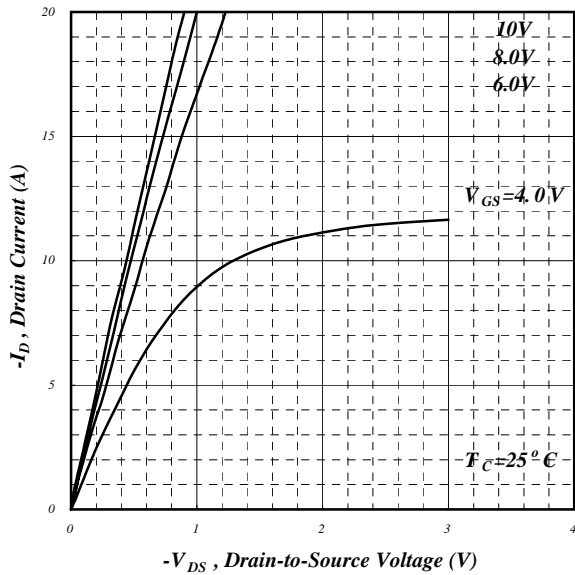


Fig 1. Typical Output Characteristics

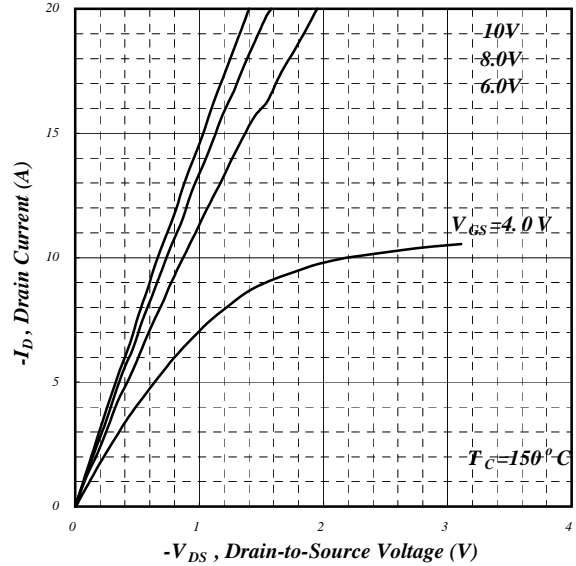


Fig 2. Typical Output Characteristics

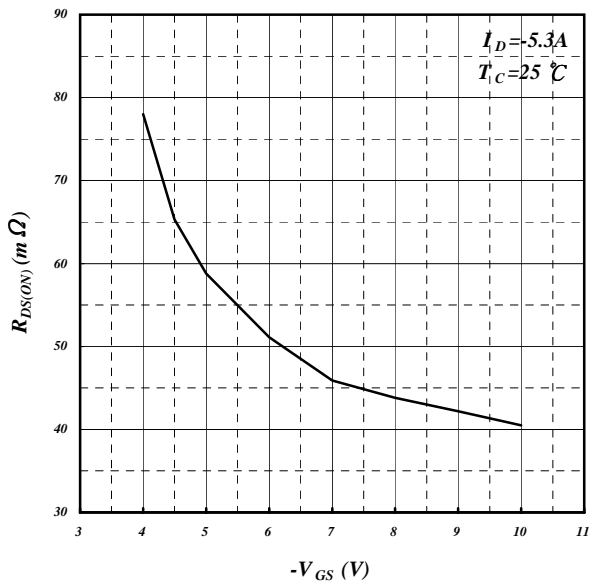


Fig 3. On-Resistance v.s. Gate Voltage

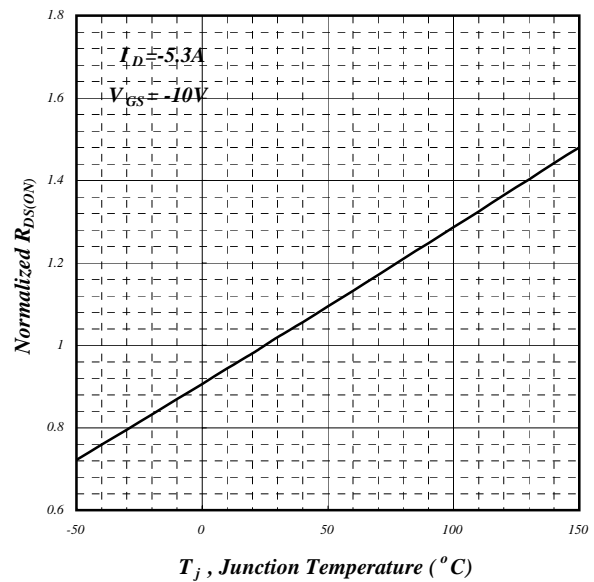


Fig 4. Normalized On-Resistance v.s. Junction Temperature





P-Channel

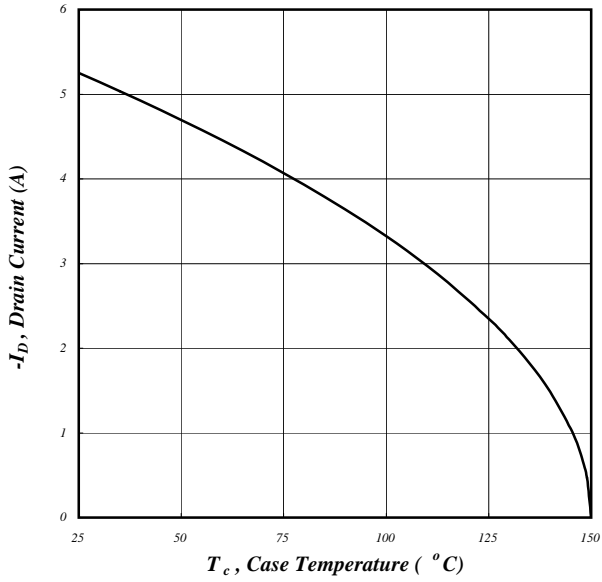


Fig 5. Maximum Drain Current v.s. Case Temperature

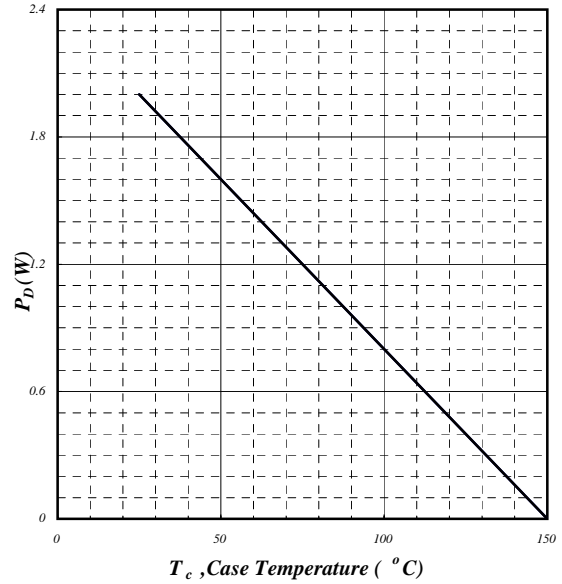


Fig 6. Typical Power Dissipation

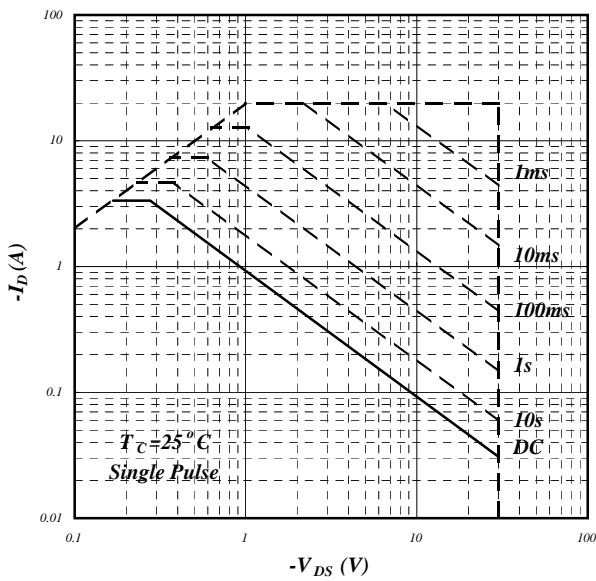


Fig 7. Maximum Safe Operating Area

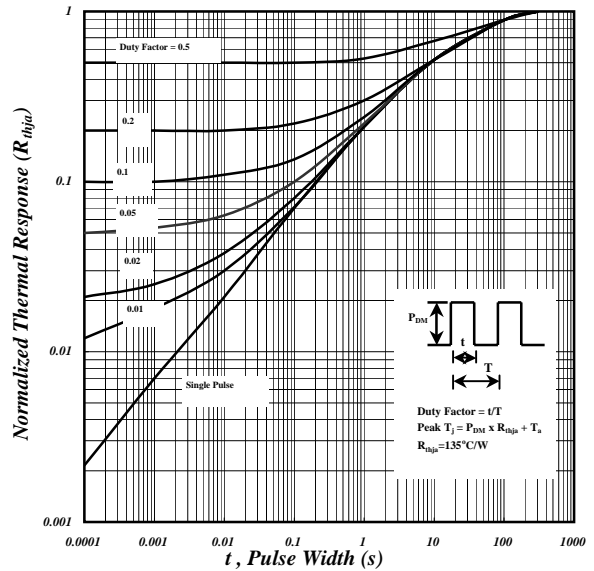


Fig 8. Effective Transient Thermal Impedance



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## P-Channel

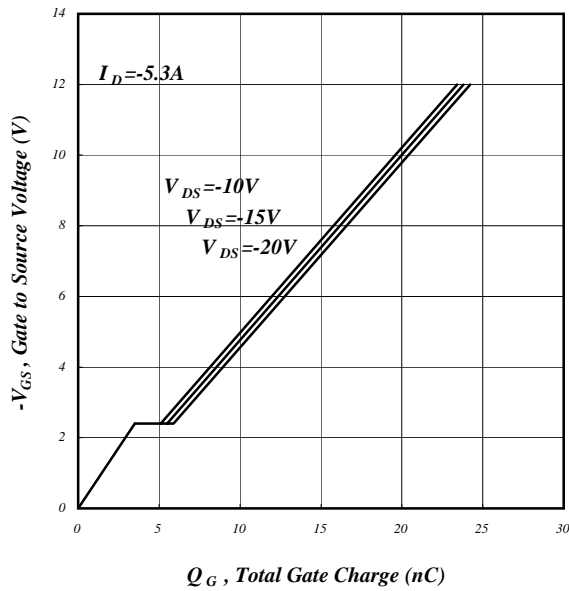


Fig 9. Gate Charge Characteristics

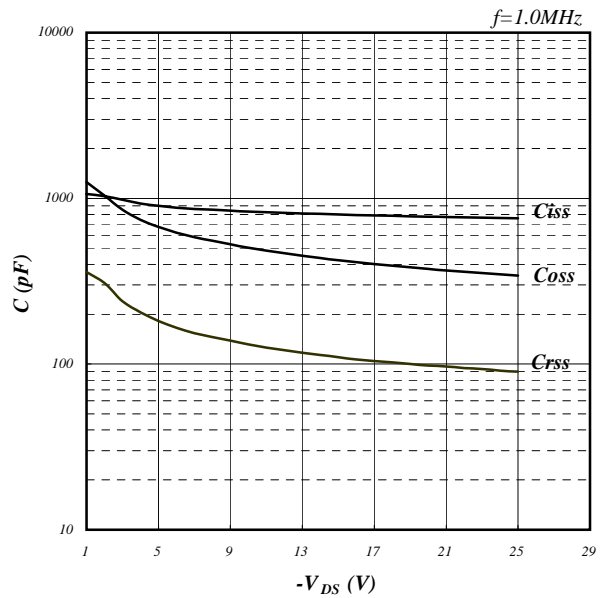


Fig 10. Typical Capacitance Characteristics

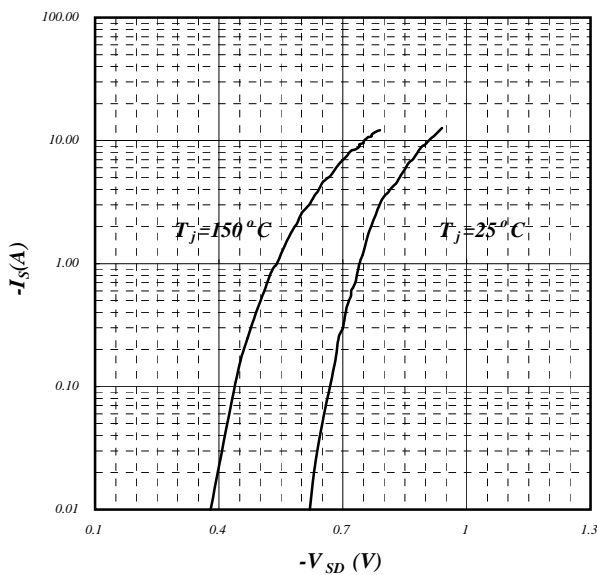


Fig 11. Forward Characteristic of Reverse Diode

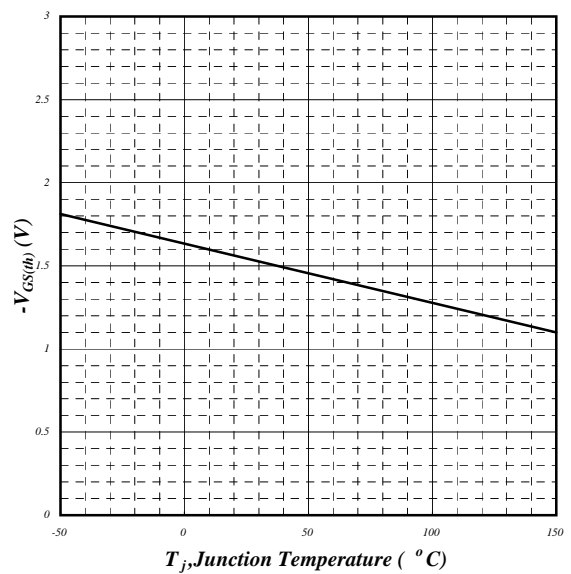


Fig 12. Gate Threshold Voltage v.s. Junction Temperature



P-Channel

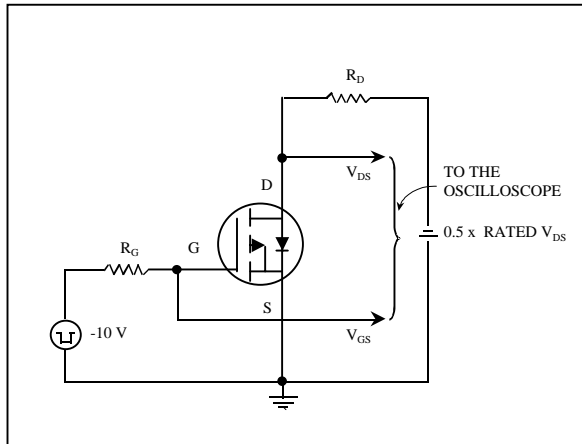


Fig 13. Switching Time Circuit

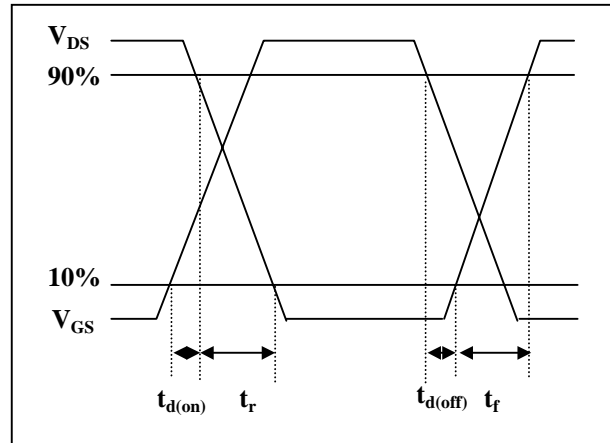


Fig 14. Switching Time Waveform

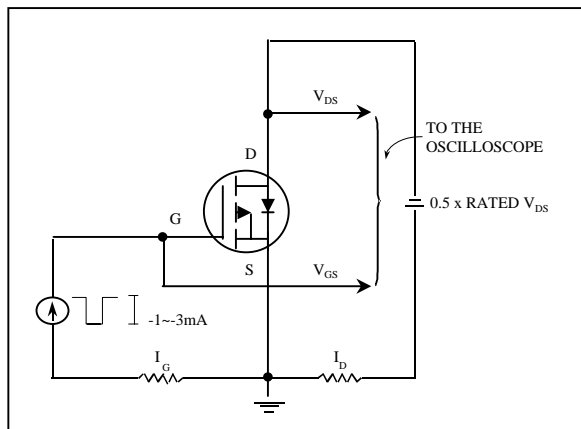


Fig 15. Gate Charge Circuit

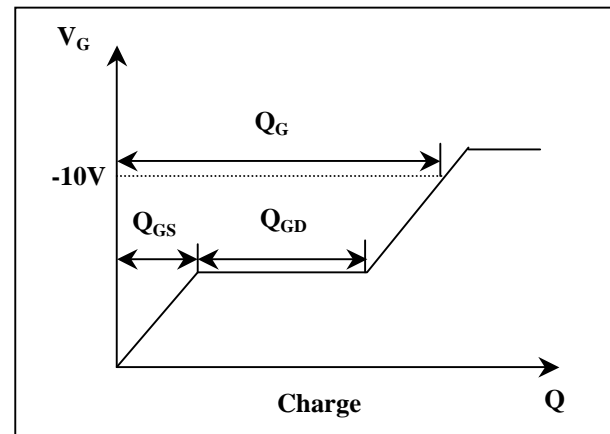


Fig 16. Gate Charge Waveform